

# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT** ( Not for submission under 37 CFR 1.99)

Application Number	10595686
Filing Date	2006-12-27
First Named Inventor	CHOY et al.
Art Unit	2881
Examiner Name	
Attorney Docket Number	1751-0405

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/R.L./	3	6162530	A	2000-12-19	XIAO, et al.	
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> ( Not for submission under 37 CFR 1.99)	Application Number		10595686	10595686 - GAU: 4181
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/R.L./	1	David S. BOYLE, et al., "Novel low temperature solution deposition of perpendicularly orientated rods of ZnO: substrate effects and evidence of the importance of counter-ions in the control of the crystallite growth", Chem. Commun., 2002, pp. 80-81, The Royal Society of Chemistry.	<input type="checkbox"/>
/R.L./	2	Kuveshni GOVENDER, et al., "Room-Temperature Lasing Observed from ZnO Nanocolumns Grown by Aqueous Solution Deposition", Advanced Materials, September 3, 2002, pp.1221-1224, Vol. 14, No. 17, Wiley-VCH Verlag GmbH & Co. KGaA, Weinheim.	<input type="checkbox"/>
/R.L./	3	Michael HUANG, et al., "Room-Temperature Ultraviolet Nanowire Nanolasers", Science Magazine, June 8, 2001, pp. 1897-1899, Vol. 292.	<input type="checkbox"/>
/R.L./	4	H.J. KO, et al., "Biexciton emission from high-quality ZnO films grown on epitaxial GaN by plasma-assisted molecular-beam epitaxy", Applied Physics Letters, July 24, 2000, pp. 537-539, Vol. 77, No. 4, American Institute of Physics.	<input type="checkbox"/>
/R.L./	5	Wen-Jun LI, et al., "Growth mechanism and growth habit of oxide crystals", Journal of Crystal Growth, 1999, pp. 186-196, Vol. 203, Elsevier Science B.V.	<input type="checkbox"/>
/R.L./	6	K. MATSUBARA, et al., "Epitaxial growth of ZnO thin films on LiNbO3 substrates", Thin Solid Films, 1999, pp. 238-240, Vol. 347, Elsevier Science S.A.	<input type="checkbox"/>
/R.L./	7	J. F. MUTH, et al., "Excitonic structure and absorption coefficient measurements of ZnO single crystal epitaxial films deposited by pulsed laser deposition", Journal of Applied Physics, June 1, 1999, pp. 7884-7887, Vol. 85, No. 11, American Institute of Physics.	<input type="checkbox"/>
/R.L./	8	Ahmed NAHHAS, et al., "Epitaxial growth of ZnO films on Si substrates using an epitaxial GaN buffer", Applied Physics Letters, March 12, 2001, pp. 1511-1513, Vol. 78, No. 11, American Institute of Physics.	<input type="checkbox"/>

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<b>Receipt date: 07/26/2007</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <b>( Not for submission under 37 CFR 1.99)</b>	Application Number		10595686	10595686 - GAU: 4181
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/R.L./	9	W. I. PARK, et al., "Metal-organic vapor phase epitaxial growth of high-quality ZnO films on Al <sub>2</sub> O <sub>3</sub> (00·1)", Journal of Materials Research, May 2001, pp. 1358-1362, Vol. 16, No. 5, Materials Research Society.	<input type="checkbox"/>
/R.L./	10	Lubomir SPANHEL, et al., "Semiconductor Clusters in the Sol-Gel Process: Quantized Aggregation, Gelation, and Crystal Growth in Concentrated ZnO Colloids", Journal of American Chemical Society, 1991, pp. 2826-2833, Vol. 113, American Chemical Society.	<input type="checkbox"/>
/R.L./	11	Zhengrong R. TIAN, et al., "Biomimetic Arrays of Oriented Helical ZnO Nanorods and Columns", Journal of American Chemical Society, 2002, pp. 12954-12955, Vol. 124, American Chemical Society.	<input type="checkbox"/>
/R.L./	12	Lionel VAYSSIERES, et al., "Purpose-Built Anisotropic Metal Oxide Material: 3D Highly Oriented Microrod Array of ZnO", Journal of Physical Chemistry, 2001, pp. 3350-3352, Vol. 105, American Chemical Society.	<input type="checkbox"/>
/R.L./	13	B. WESSLER, et al., "Epitaxial growth of ZnO thin films on ScAlMgO <sub>4</sub> (0001) by chemical solution deposition", Journal of Crystal Growth, 2002, pp. 283-292, Vol. 242, Elsevier Science B.V.	<input type="checkbox"/>
/R.L./	14	Aishi YAMAMOTO, et al., "Biexciton luminescence in high-quality ZnO epitaxial thin films", Journal of Applied Physics, November 15, 2001, pp. 4973-4976, Vol. 90, No. 10, American Institute of Physics.	<input type="checkbox"/>

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Examiner Signature	/Rebecca Lee/	Date Considered	10/09/2008
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- ☐ See attached certification statement.
- ☐ Fee set forth in 37 CFR 1.17 (p) has been submitted herewith.
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A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature	/gfr4/	Date (YYYY-MM-DD)	2007-07-24
Name/Print	G. Franklin Rothwell	Registration Number	18125

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